PC	N Number:	20181	0181211000.2								PCI	N Date	<b>1</b>	Dec	13,	2018	
Tit	le: Qualify I	sem	mbly Material set for Select Device(s)														
Cu	stomer Conta	anager	ager Dept: Quality				Services										
Pr	oposed 1 <sup>st</sup> Shi	<b>::</b> ]	: June 13, 2019				Estimated Sample Date provided at Availability: sample request					ed at Jest					
Change Type:																	
	Assembly Site				Design						Wafe	r Bu	imp S	Site			
	Assembly Proc			Data Sheet							Wafe	Wafer Bump Material					
$\square$	Assembly Mate	erials				Part	nι	imber cl	nang	ge		Wafe	lafer Bump Process				
	Mechanical Specification					Test	Si	Site Wafer				r Fa	r Fab Site				
Packing/Shipping/Labeling						Test	: Pr	ocess				Wafe	r Fa	b Ma	teria	als	
										Wafer Fab Process							
PCN Details																	
De	scription of C	hange															
Texas Instruments is pleased to announce the qualification of new assembly material for devices listed in "Product affected" section below. Devices will remain in current assembly facility and piece part changes as follows:																	
		Current					:				Proposed						
Ν	lount compoun	d	00101335950							101339368							
Ν	lold Compound	10132339					)7			1013			376660				
L	ead frame finis	NiPdAu						N	NiPdAu (Single side roughened)								
Re	Reason for Change:																
Со	ntinuity of Sup	ply															
An	Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																
No	ne																
Anticipated impact on Material Declaration																	
No Impact to the Material Declaration				Material Declarations or Product Content reports are driven from production data and will be available following the production release. Upon production release the revised reports can be obtained from the <u>TI Eco-Info website</u> . There is no impact to the material meeting current regulatory compliance requirements with this PCN change.							5						
Changes to product identification resulting from this PCN:																	
None																	
Product Affected:																	
HBCD412ATDKDRHB TAS5414ATDK						OKDQ1		TAS	541	4BTDK	DRQ1	1 TA	S54	24AT	DKD	RQ1	ן
HBCD412ATDKDRHBG4 TAS54					414ATDKDQ1G4 TAS5424/				4ATDK	TDKDMQ1 TAS5424ATDKDRQ1G				RQ1G4			
Н	BCD412CTDKDR	RHB	TAS	5414	414ATDKDRMQ1 TAS5424AT				4ATDK	DKDQ1 TAS5424BTDKDRQ1							
TAS5414ATDKDMQ1 TAS5414ATDKI						OKDRÇ	<u>1</u>	TAS	542	4ATDK	DRM	Q1 TA	S55	14BT	DKD	RQ1	

# **Qualification Report** Approve Date 26-Nov-2018

# **Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name / Condition	Duration	QBS Device: TAS5424B TDKERQ1	QBS Device: TAS5424B TDKDRQ1	QBS Device: CODPHD P2DKAR	QBS Device: CODC2PS A2DKPR
TEST GRC	OUP A	– ACCELERATED EN'	VIRONME	NT ST	RESS TESTS					
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Auto Preconditioning	See Notes	3/385/0	3/963/0	3/492/0	3/231/0
THB/HA ST	A2	JEDEC JESD22- A101 or A110	3	77	Temperature- Humidity-Bias or Biased HAST, 130C	96 Hours	3/231/0	3/231/0	3/231/0	-
AC/UHA ST	A3	JEDEC JESD22- A102 or A118 or A101	3	77	Autoclave or Unbiased HAST Or Temperature- Humidity, 121C	96 Hours	3/231/0	3/231/0	-	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	60	Post Temp. Cycle, Bond Pull	Wires	3/180/0	1/60/0	3/180/0	3/180/0
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle, -40C/105C	1000 Cycles	1/45/0	1/45/0	-	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life, 150C	1000 Hours	3/135/0	3/135/0	-	-
TEST GROUP B – ACCELERATED LIFETIME SIMULATION TESTS										
HTOL	B1	JEDEC JESD22- A108	3	80 0	High Temperature Operating Life, 125C	1000 Hours	3/231/0	-	1/77/0	2/254/0
ELFR	B2	AEC Q100-008	3	77	Early Life Failure Rate, 150C	24 Hours	3/2400/0	-	3/2400/0	-
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life		-	-	-	-
TEST GRC	OUP C	– PACKAGE ASSEMB		RITY	TESTS					
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	3/90/0	-	-	-
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	3/90/0	-	-	-
SD	C3	JEDEC JESD22- B102	1	15	Surface Mount Solderability >95% Lead Coverage	8 Hours Steam Age	1/15/0	-	-	-
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions (Cpk>1.67)		3/30/0	-	-	-
LI	C6	JEDEC JESD22- B105	1	50	Lead Integrity	Leads	-	-	-	-
TEST GRC	OUP D	- DIE FABRICATION I	RELIABILI	ΤΥ ΤΕ	STS					
EM	D1	JESD61	-	-	Electromigration	Completed Per Process Technology Requireme	-	-	-	-

						nts				
						Completed				
		150005			Time Dependant	Per				
	50					Process				
IDDB	D2	JESD35	-	-	Dielectric	Technology	-	-	-	-
					Breakdown	Requireme				
						nts				
-						Completed				
						Per				
					Hot Injection	Process				
HCI	D3	JESD60 & 28	-	-	Carrier	Technology	-	-	-	-
					Carrier	Requireme				
						nts				
						Completed				
						Por				
					Negative Bias	Process				
NBTI	D4	-	-	-	Temperature	Technology	-	-	-	-
					Instability	Boguiromo				
						ntequileme				
						Tits Completed				
						Completed				
						Per				
SM	D5	-	-	-	Stress Migration	Process	-	-	-	-
						Technology				
						Requireme				
						nts				
TEST GRC	DUP E	– ELECTRIOCAL VER	IFICATIO	N TES	TS					
					Pre- and Post-					
TEST	E1		-	-	Stress		_	_	_	_
1201					Functional/Param					
					eter					
					Electrostatic					
HBM	E2	AEC Q100-002	-	-	Discharge Human		-	-	1/3/0	1/3/0
					Body Model					
					Electrostatic					
CDM	<b>F</b> 0				Discharge			1/2/0	1/0/0	1/2/0
CDM	E3	AEC Q100-011	-	-	Charged Device		-	1/3/0	1/3/0	1/3/0
					Model					
LU	E4	AEC Q100-004	-	-	Latch-Up		-	-	1/6/0	1/6/0
		AFC Q100-00			Electrical					
ED	E5	AFC 0003	-	-	Distributions		-	-	3/90/0	3/90/0
FG	E6	AEC 0100-007	_	_	Eault Grading		_		_	_
	E7				Characterization			-		-
CHAR		AEC QUUS	-	-			-	-	-	-
EMC	E9	SAE J1752/3	-	-	Electromagnetic		-	-	-	-
					Compatibility					
SC	E1	AFC Q100-012	-	-	Short Circuit		-	-	-	-
	0				Characterization					
IF	E1	AEC 0005	_	-	Lead (Ph) Free		-	_	-	-
 	2									
ADDITION	AL TE	STS								
						per				
MO					Manufacturability	automotive	DAGO	DACC	DAGO	DACC
IVIQ				-	(Auto Assembly)	requirement	PASS	PA55	PASS	PA55
						s				
===					Thermal Integrity	10.01-5	0/20/-			
IIS					Sequence	L3-245C	3/36/0	-	-	-
Q006				-	Cu Wire – Q006		PASS	-	PASS	PASS
2000							00			

Notes: - QBS Device TAS5424BTDKERQ1 is qualified at LEVEL3-245CG

- QBS Device TAS5424BTDKDRQ1 is qualified at LEVEL3-245CG

- QBS Device CODPHDP2DKAR is qualified at LEVEL3-260CG

- QBS Device CODC2PSA2DKPR is qualified at LEVEL3-260CG

#### A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

#### Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

## E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

## Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

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